In the Claims:

1. (currently amended) A method for forming ultra shallow junctions, comprising:

providing a semiconductor;

implanting a dopant species into said semiconductor; and

annealing said implanted semiconductor with an ultra high temperature anneal comprising annealing temperatures from ~~1150°~~ about 1050°C to about 1350°C for a period of from about 0.5 milliseconds to about 3 milliseconds..

2. (previously presented) The method of claim 1 further comprising an amorphizing implant.

3. (previously presented) The method of claim 2 wherein said amorphizing implant comprises implanting a species from the group consisting of silicon, germanium, antimony, indium, arsenic, neon, argon, krypton, and xenon.

4-18 (canceled)

19. (new) The method of claim 1 wherein said annealing temperature is in the range of from about 1150°C to about 1350°C.